

Power Electronics Semiconductor Devices

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Edited by
Robert Perret

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Table of Contents

Preface	xi
Chapter 1. Power MOSFET Transistors	1
Pierre ALOÏSI	
1.1. Introduction.	1
1.2. Power MOSFET technologies.	5
1.2.1. Diffusion process	5
1.2.2. Physical and structural MOS parameters	7
1.2.3. Permanent sustaining current	20
1.3. Mechanism of power MOSFET operation.	23
1.3.1. Basic principle	23
1.3.2. Electron injection	23
1.3.3. Static operation	25
1.3.4. Dynamic operation	30
1.4. Power MOSFET main characteristics	34
1.5. Switching cycle with an inductive load	36
1.5.1. Switch-on study	36
1.5.2. Switch-off study	38
1.6. Characteristic variations due to MOSFET temperature changes.	44
1.7. Over-constrained operations.	46
1.7.1. Overvoltage on the gate	46
1.7.2. Over-current	47
1.7.3. Avalanche sustaining.	49
1.7.4. Use of the body diode	50
1.7.5. Safe operating areas	51
1.8. Future developments of the power MOSFET.	53
1.9. References	55

Chapter 2. Insulated Gate Bipolar Transistors	57
Pierre ALOÏSI	
2.1. Introduction.	57
2.2. IGBT technology	58
2.2.1. IGBT structure	58
2.2.2. Voltage and current characteristics	60
2.3. Operation technique.	63
2.3.1. Basic principle	63
2.3.2. Continuous operation	64
2.3.3. Dynamic operation	71
2.4. Main IGBT characteristics	74
2.5 One cycle of hard switching on the inductive load	75
2.5.1. Switch-on study	76
2.5.2. Switch-off study	78
2.6 Soft switching study	86
2.6.1. Soft switching switch-on: ZVS (Zero Voltage Switching).	86
2.6.2. Soft switching switch-off: ZCS (Zero Current Switching).	88
2.7. Temperature operation	94
2.8. Over-constraint operations	98
2.8.1. Overvoltage	98
2.8.2. Over-current	99
2.8.3. Manufacturer's specified safe operating areas	113
2.9. Future of IGBT.	116
2.9.1. Silicon evolution	116
2.9.2. Saturation voltage improvements	117
2.10. IGBT and MOSFET drives and protections	119
2.10.1. Gate drive design	119
2.10.2. Gate drive circuits.	122
2.10.3. MOSFET and IGBT protections	128
2.11. References.	130
Chapter 3. Series and Parallel Connections of MOS and IGBT	133
Daniel CHATROUX , Dominique LAFORE and Jean-Luc SCHANEN	
3.1. Introduction.	133
3.2. Kinds of associations	134
3.2.1. Increase of power	134
3.2.2. Increasing performance	135
3.3. The study of associations: operation and parameter influence on imbalances in series and parallel	135
3.3.1. Analysis and characteristics for the study of associations	135
3.3.2. Static operation	137

3.3.3. Dynamic operation: commutation	140
3.3.4. Transient operation	149
3.3.5. Technological parameters that influence imbalances	151
3.4. Solutions for design	152
3.4.1. Parallel association	152
3.4.2. Series associations	161
3.4.3. Matrix connection of components	179
3.5. References	182
Chapter 4. Silicon Carbide Applications in Power Electronics	185
Marie-Laure LOCATELLI and Dominique PLANSON	
4.1. Introduction	185
4.2. Physical properties of silicon carbide	186
4.2.1. Structural features	186
4.2.2. Chemical, mechanical and thermal features	189
4.2.3. Electronic and thermal features.	188
4.2.4. Other “candidates” as semiconductors of power.	195
4.3. State of the art technology for silicon carbide power components.	296
4.3.1. Substrates and thin layers of SiC.	296
4.3.2. Technological steps for achieving power components	203
4.4. Applications of silicon carbide in power electronics.	216
4.4.1. SiC components for high frequency power supplies	216
4.4.2. SiC components for switching systems under high voltage and high power	233
4.4.3. High energy SiC components for series protection systems	249
4.5. Conclusion	252
4.6. Acknowledgments.	255
4.7. References	255
Chapter 5. Capacitors for Power Electronics	267
Abderrahmane BÉROUAL, Sophie GUILLEMET-FRITSCH and Thierry LEBEY	
5.1. Introduction.	267
5.2. The various components of the capacitor – description	268
5.2.1. The dielectric material	269
5.2.2. The armatures	269
5.2.3. Technology of capacitors	270
5.2.4. Connections	271
5.3. Stresses in a capacitor.	272
5.3.1. Stresses related to the voltage magnitude.	272
5.3.2. Losses and drift of capacity	273
5.3.3. Thermal stresses	274

5.3.4. Electromechanical stresses	275
5.3.5. Electromagnetic constraints	276
5.4. Film capacitors	276
5.4.1. Armatures	276
5.4.2. Dielectric materials	279
5.5. Impregnated capacitors	279
5.6. Electrolytic capacitors	280
5.7. Modeling and use of capacitors	282
5.7.1. Limitations of capacitors	283
5.7.2. Application of capacitors	290
5.8. Ceramic capacitors	293
5.8.1. Definitions	294
5.8.2. Methods of producing ceramics	296
5.8.3. Technologies of ceramic capacitors	299
5.8.4. The different types of components	302
5.8.5. Summary – conclusion	310
5.9. Specific applications of ceramic capacitors in power electronics	311
5.9.1. Snubber circuits	311
5.9.2. In ZVS	312
5.9.3. Series resonant converters	313
5.10. R&D perspectives on capacitors for power electronics	313
5.10.1. Film capacitors	313
5.10.2. Electrolytic capacitors	314
5.10.3. Ceramic capacitors	314
5.11. References	315
Chapter 6. Modeling Connections	317
Edith CLAVEL, François COSTA, Arnaud GUENA, Cyrille GAUTIER, James ROUDET and Jean-Luc SCHANEN	
6.1. Introduction	317
6.1.1. Importance of interconnections in power electronics	317
6.1.2. The constraints imposed on the interconnections	318
6.1.3. The various interconnections used in power electronics	319
6.1.4. The need to model the interconnections	320
6.2. The method of modeling	321
6.2.1. The required qualities	321
6.2.2. Which method of modeling?	322
6.2.3. Brief description of the PEEC method	324
6.3. The printed circuit board	329
6.3.1. Introduction	330
6.3.2. Thin wire method	330

6.3.3. Expressions of per unit length parameters	332
6.3.4. Representation by multi-poles, “circuit” modeling	340
6.3.5. Topological analysis of printed circuit	346
6.3.6. Experimental applications.	349
6.3.7. Conclusion on the simulation of printed circuit	353
6.4. Towards a better understanding of massive interconnections	353
6.4.1. General considerations.	353
6.4.2 The printed circuit board or the isolated metal substrate (IMS)	359
6.4.3. Massive conductors.	361
6.4.4. Bus bars	361
6.5. Experimental validations	362
6.6. Using these models	366
6.6.1. Determination of equivalent impedance	366
6.6.2. Other applications: towards thermal analysis and electrodynamic efforts computation	390
6.7. Conclusion	399
6.8. References	400
Chapter 7. Commutation Cell.	403
James ROUDET and Jean-Luc SCHANEN	
7.1. Introduction: a well-defined commutation cell	403
7.2. Some more or less coupled physical phenomena.	404
7.3. The players in switching (respective roles of the component and its environment)	410
7.3.1. Closure of the MOSFET.	411
7.3.2. Opening of the MOSFET	424
7.3.3. Summary	431
7.4. References	432
Chapter 8. Power Electronics and Thermal Management	433
Corinne PERRET and Robert PERRET	
8.1. Introduction: the need for efficient cooling of electronic modules	433
8.2. Current power components	436
8.2.1. Silicon chip: the active component	436
8.2.2. Distribution of losses in the silicon chip	442
8.3. Power electronic modules	442
8.3.1. Main features of the power electronic modules	442
8.3.2. The main heat equations in the module	444
8.3.3. Cooling currently used for components of power electronics	446
8.3.4. Towards an “all silicon” approach	448
8.3.5. Conclusion	451

8.4. Laws of thermal and fluid exchange for forced convection with single phase operation	452
8.4.1. Notion of thermal resistance	452
8.4.2. Laws of convective exchanges from a thermal and hydraulic point of view: the four numbers of fluids physics	456
8.5. Modeling heat exchanges.	461
8.5.1. Semi-analytical approach	461
8.5.2. The numerical models	472
8.5.3. Taking into account electro-thermal coupling	478
8.6. Experimental validation and results	486
8.6.1. Infrared thermography	486
8.6.2. Indirect measurement of temperature from a thermo-sensible parameter	490
8.7. Conclusion	493
8.8. References	494
Chapter 9. Towards Integrated Power Electronics	497
Patrick AUSTIN, Marie BREIL and Jean-Louis SANCHEZ	
9.1. The integration	497
9.1.1. Introduction	497
9.1.2. The different types of monolithic integration	499
9.2. Examples and development of functional integration	507
9.2.1. The MOS thyristor structures	507
9.2.2. Evolution towards the integration of specific functions	514
9.3. Integration of functions within the power component	520
9.3.1. Monolithic integration of electrical functions	520
9.3.2. Extensions of integration	530
9.4. Design method and technologies	535
9.4.1 Evolution of methods and design tools for functional integration	535
9.4.2. The technologies	537
9.5. Conclusion	541
9.6. References	542
List of Authors	547
Index	551

Preface

Electrical consumption, especially direct or variable frequency currents, has strongly increased over 50 years in industry. This situation explains the growth of power electronics.

At the beginning, when rectifiers replaced DC machines, only diodes and thyristors were used. Then power transistors appeared and enabled the extension of smaller power applications for domestic use. New research topics were developed around converters and power devices. For all these years, circuit specialists used available components but did not try to improve them; a lot of progress in device manufacturing proceeded from microelectronic technology.

At the beginning of the 21st century it appeared necessary to bring component researchers and circuit specialists closer together to create a global conception approach.

For over 15 years, French industrialists and academics have combined their efforts in the GIRCEP (Groupement Industriel et de Recherche sur les Composants Electroniques de Puissance) to develop, with the help of CNRS (Centre National de Recherche Scientifique – France), research programs in power electronics. Power Electronics Semiconductor Devices is a product of this work.

The first and second chapters are devoted to up-to-date switches (MOSFET and IGBT). Their properties and limitations are presented by P. Aloisi.

In Chapter 3, D. Chatroux and J.L. Schanen explain how to increase current or voltage with serial or parallel associations of elementary components.

M.L. Locatelli and D. Planson present a prospective study on new silicone carbide devices in Chapter 4. Possible performance improvements are shown as well as the technological difficulties linked to the production and process of the material.

Chapter 5 is devoted to a passive component essential for static converters; power capacitors working at high frequency. The authors are A. Bérroual, S. Guillemet and Th. Lebey.

Power electronics must use conductors that allow the movement of large currents with a parasitic inductance as low as possible. A model for a good design of these conductors is described by E. Clavel, F. Costa, C. Gauthier, A. Guéna, J. Roudet and JL. Schanen in Chapter 6.

The operation of converters is often explained by the switching cell concept defined by H. Foch [FOC88] in the 1980s. The right understanding of its operation and fine modeling are shown in Chapter 7, written by J. Roudet and JL. Schanen.

In Chapter 8, thermal aspects relating to the use of power electronic devices are developed by C. Perret and R. Perret with the help of J.M. Dorkel. The main problems related to cooling and examples of modeling are described.

Finally, in Chapter 9, P. Austin, M. Breil and JL. Sanchez show the value of integration on silicon for power electronic modules. From industrial achievements and laboratory prototypes they provide progressive ideas that can lead to a profound evolution of power electronics.

The book lacks at least one chapter: one which deals with magnetic components for power electronics. Several recent studies have been developed in laboratories; interested readers may consult [KER03] and [LAO04] for further information on current developments.

This book on power electronic devices represents a summary of research carried out in French and international laboratories in the early years of the 21st century.

Robert Perret

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